## **REFERENCE NUMERALS**

## 8327/ETCH/SILICON

SEQUENCE	100
Step	101
Step	102
Step	104
Step	106
Step	108
Step	110
Step	112
Step	114
Step	116
Step	117
Step	118
Substrate	200
Film stack	202
Surface	203
Gate dielectric layer	204
Sidewalls	205
Gate electrode layer	206
Layer	207
Width	209
Width	211
Patterned mask	212
Anti-reflective coating (ARC)	
Hard mask layer	214
Width	215
Gate electrode	216
Thickness	217
Polysilicon electrode traces	218
Hard mask	219
Traces	220
Regions	232
Regions	234
Channel region	236
Reactor	300
Process chamber	310
Coil element	312
Semiconductor wafer	314
Wafer support pedestal	316
Plasma power source	318
Network	319
Flat dielectric ceiling	320
	0

Biasing power source	322	
Second matching network		
Entry ports	326	
Throttle valve	327	
Conductive body (wall)	330	
Electrical ground	334	
Vacuum pump	336	
Gas panel	338	
Controller	340	
Memory	342	
CPU	344	
Support circuits	346	
Gas source	348	
Gas conduit	349	
Gaseous mixture	350	
Plasma	355	
AXIOM reactor	400	
Process chamber	402	
Substrate pedestal	404	
Remote plasma source	406	
Controller	408	
Portion	410	
Second portion	412	
Vacuum pump	414	
Sidewall	416	
Lid	418	400
Gas distribution plate Gas mixing volume		420
Reaction volume	422 424	
Substrate (wafer)	424	
Gas-filled lamps	428	
Heater	430	
Conduit	432	
Source	434	
Exhaust port	436	
Throttle valve	438	
Support systems	440	
Remote plasma chamber	442	
Gas panel	444	
Power source	446	
RF generator	448	
Tuning assembly	450	
Applicator	452	
CPU	454	
Memory	456	
Support circuits	458	
Ground reference	460	

Plasma	462
Process gas	464
Conduit	466
Inlet port	468
Openings	470
Processing system	500
Input/output mole	502
Measuring station	504
FOUP	506
Robot	508
Process modules	510
Process modules	512
process modules	514
Process modules	516
Process modules	519
Robot	520
Load-lock chambers	522
Interface	524
Metrology module	526
Vacuumed plenum	528
Robot	530
Wafer receptacle	534
Handling device	536
Track	538
System controller	540
CPU	542
Memory	544
Support circuit	546

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